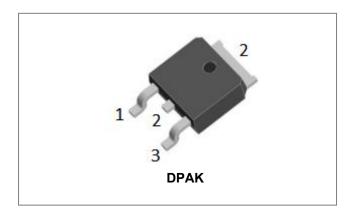


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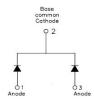
MBRD20200CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =105°C, rectangular wave form	10(peg leg) 20(peg device)	Α
Peak One Cycle Non-Repetitive Surge Current(peg leg)	I _{FSM}	8.3 ms, half Sine pulse	120	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.90	1.00	V
(per leg) *	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.80	0.90	V
Reverse Current (per leg) *	I _{R1}	I_{R1} @V _R = rated V _R , T _J = 25 °C		10	uA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.02	10	mA
Junction Capacitance(per leg)	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C, f_{SIG} = 1MHz$	100	150	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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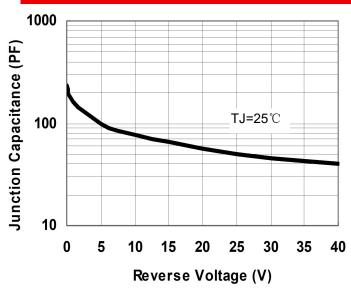




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to + 150	°C
Typical Thermal Resistance Junction to Case	R _θ JC	-	3.5	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves



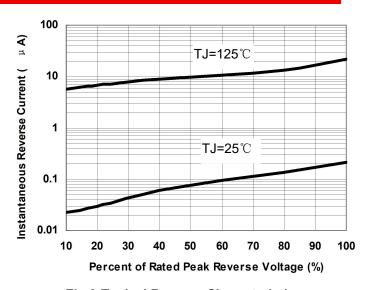


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

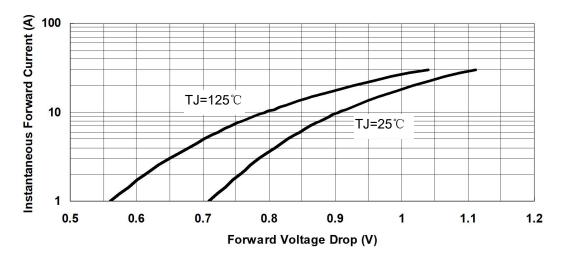


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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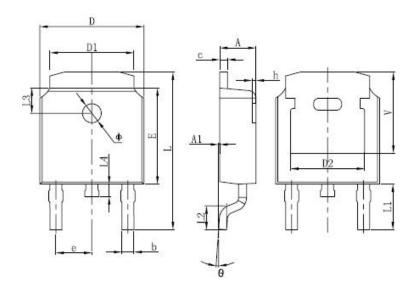


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Mechanical Dimensions DPAK



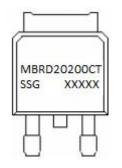
CVMDOL	Millimeters			
SYMBOL	MIN.	Тур	MAX.	
Α	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D1	4.95	-	5.46	
D2	4.32	-	-	
E	5.97	6.1	6.22	
е	2.29BSC			
L	9.4	-	10.41	
L1	2.90 REF.			
L2	1.4	1.52	1.78	
L3	1.60 REF.			
L4	-	-	1.02	
Ф	1.1	-	1.3	
Θ	0°	-	10°	
V	5.21	-	-	

Ordering Information

Device	Package	Shipping
MBRD20200CT	DPAK (Pb-Free)	2500pcs / reel
MBRD20200CTTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type
D = Package type
20 = Forward Current (20A)
200 = Reverse Voltage (200V)
CT = Configuration

 SSG
 = SSG

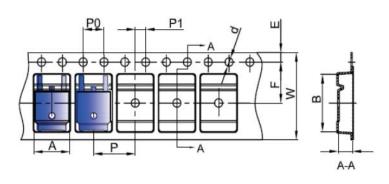
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



SYMBOL	Millimeters		
STWIDOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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MBRD20200CT



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